

Silicon PNP Power Transistors

2SA775

DESCRIPTION

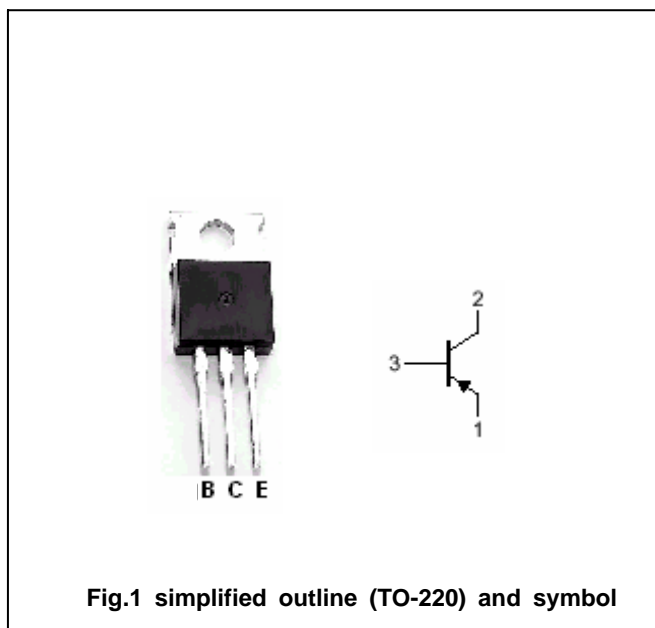
- With TO-220 package
- High breakdown voltage

APPLICATIONS

- For TV vertical output amplifier applicatons

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current		-0.7	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	12.5	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10 μ A, I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10 μ A, I _C =0	-4			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1.0	μ A
h _{FE}	DC current gain	I _C =-50mA; V _{CE} =-4V	50			
f _T	Transition frequency	I _C =-50mA; V _{CE} =-4V		30		MHz

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ±0.10 mm)